

## SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE: 20 TO 40 VOLTS

CURRENT: 1.0 AMPERES

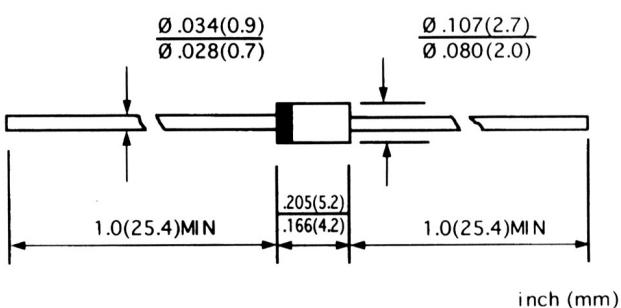
## FEATURES

- Metal-Semiconductor junction with guard ring
- Epitaxial construction
- Low forward voltage drop, Low switching losses
- High surge capability
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- The plastic material carries U/L recognition 94V-O

## MECHANICAL DATA

Case: JEDEC DO-41, molded plastic  
 Terminals: Axial leads, solderable per MIL-STD-202,  
 Method 208  
 Polarity: Color band denotes cathode  
 Weight: 0.012 ounce, 0.34 gram  
 Mounting position: Any

## DO-41



inch (mm)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameters		1N5817	1N5818	1N5819	UNITS
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	20	30	40	V
Maximum RMS Voltage	V <sub>RMS</sub>	14	21	28	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	30	40	V
Maximum Average Forward Rectified Current 9.5mm Lead Length, @ T <sub>A</sub> =90°C	I <sub>(AV)</sub>		1.0		A
Peak Forward Surge Current @ T <sub>j</sub> =70°C 8.3ms Single half-sine-wave superimposed on rated load	I <sub>FSM</sub>		25		A
Maximum Instantaneous Forward Voltage at 1.0A at 3.0A(Note 1)	V <sub>F</sub>	0.450	0.550	0.600	V
		0.750	0.875	0.900	
Maximum Reverse Current @ T <sub>A</sub> =25°C at Rated DC Blocking Voltage @ T <sub>A</sub> =100°C	I <sub>R</sub>	1.0 10.0			mA
Typical Junction Capacitance (Note 2)	C <sub>j</sub>	110			pF
Typical Thermal Resistance (Note 3)	R <sub>θJA</sub>	50			°C/W
Operating Junction Temperature Range	T <sub>j</sub>	-65---+150			°C
Storage Temperature Range	T <sub>STG</sub>	-65---+150			°C

NOTE: 1.Pulse test: 300us pulse width, 1% duty cycle.

2.Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3.Thermal Resistance Junction to Ambient.